## 1. General description

NPN high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9560Z

#### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- · High collector current capability
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- AEC-Q101 qualified

## 3. Applications

- Electronic ballast for fluorescent lighting
- · LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- · Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

#### Table 1. Quick reference data

| Symbol           | Parameter                 | Conditions  |  | Min | Тур | Max | Unit |
|------------------|---------------------------|---|--|-----|-----|-----|------|
| V <sub>CEO</sub> | collector-emitter voltage | open base   |  | -   | -   | 600 | V    |
| I <sub>C</sub>   | collector current         |   |  | -   | -   | 0.5 | Α    |
| h <sub>FE</sub>  | DC current gain           | $V_{CE}$ = 10 V; $I_{C}$ = 50 mA; $T_{amb}$ = 25 °C |  | 70  | 135 | -   |      |



### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline               | Graphic symbol |
|-----|--------|-------------|----------------------------------|----------------|
| 1   | В      | base        | 4                                | 2, 4           |
| 2   | С      | collector   |                                  | . 🗸            |
| 3   | Е      | emitter     |                                  | 1—             |
| 4   | С      | collector   | <b>□</b> 1 <b>□</b> 2 <b>□</b> 3 | 3              |
|     |        |             | SC-73 (SOT223)                   | sym016         |

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number | Package |   |         |  |  |  |
|-------------|---------|---|---------|--|--|--|
|             | Name    | Description   | Version |  |  |  |
| PBHV8560Z   | SC-73   | plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body | SOT223  |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBHV8560Z   | HV856Z       |

### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

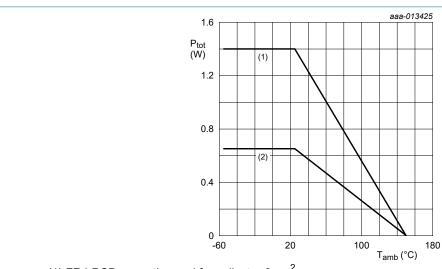
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol            | Parameter                      | Conditions               |     | Min | Max  | Unit |
|-------------------|--------------------------------|--------------------------|-----|-----|------|------|
| $V_{CBO}$         | collector-base voltage         | open emitter             |     | -   | 600  | V    |
| $V_{CEO}$         | collector-emitter voltage      | open base                |     | -   | 600  | V    |
| V <sub>CESM</sub> | collector-emitter peak voltage | V <sub>BE</sub> = 0 V    |     | -   | 600  | V    |
| V <sub>EBO</sub>  | emitter-base voltage           | open collector           |     | -   | 6    | V    |
| I <sub>C</sub>    | collector current              |                          |     | -   | 0.5  | А    |
| P <sub>tot</sub>  | total power dissipation        | T <sub>amb</sub> ≤ 25 °C | [1] | -   | 0.65 | W    |
|                   |                                |                          | [2] | -   | 1.4  | W    |
| Tj                | junction temperature           |                          |     | -   | 150  | °C   |
| T <sub>amb</sub>  | ambient temperature            |                          |     | -55 | 150  | °C   |
| T <sub>stg</sub>  | storage temperature            |                          |     | -65 | 150  | °C   |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

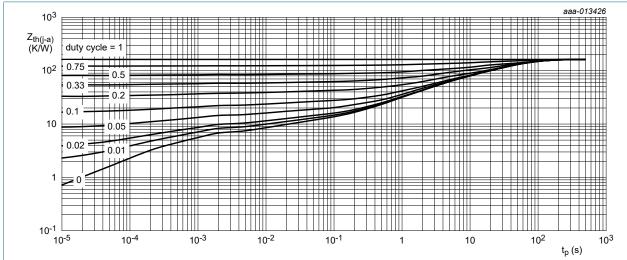
#### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

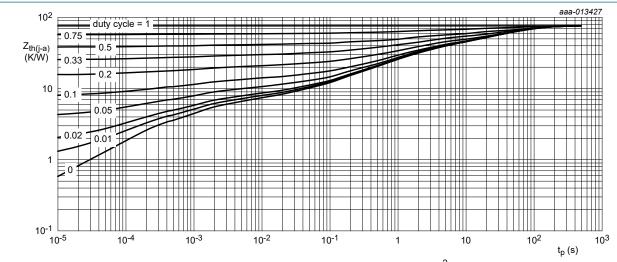
| Symbol              | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|---------------------|--|-------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$       | thermal resistance from                          | in free air | [1] | -   | -   | 190 | K/W  |
| junction to ambient |  | [2]         | -   | -   | 89  | K/W |      |
| $R_{th(j-sp)}$      | thermal resistance from junction to solder point |             |     | -   | -   | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



FR4 PCB, single-sided copper, tin-plated and standard footprint.

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

## 10. Characteristics

**Table 7. Characteristics** 

| Symbol  | Parameter   | Conditions  | Min | Тур | Max | Unit |
|---|---|---|-----|-----|-----|------|
| I <sub>CBO</sub>  | collector-base cut-off  | V <sub>CB</sub> = 400 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C   | -   | -   | 100 | nA   |
|   | current   | V <sub>CB</sub> = 400 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C  | -   | -   | 10  | μΑ   |
| I <sub>CES</sub>  | collector-emitter cut-off current   | V <sub>CE</sub> = 400 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C  | -   | -   | 100 | nA   |
| I <sub>EBO</sub>  | emitter-base cut-off current  | V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C   | -   | -   | 100 | nA   |
| h <sub>FE</sub>   | DC current gain   | V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C  | 70  | 135 | -   |      |
|   |   | $V_{CE}$ = 10 V; $I_{C}$ = 100 mA; $t_{p} \le 300 \mu s$ ;<br>δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed                         | 70  | 135 | -   |      |
| V <sub>CEsat</sub> collector-emitter saturation voltage |   | I <sub>C</sub> = 50 mA; I <sub>B</sub> = 5 mA; T <sub>amb</sub> = 25 °C   | -   | 50  | 100 | mV   |
|   | $I_C$ = 100 mA; $I_B$ = 20 mA; $t_p \le 300 \ \mu s$ ;<br>$\delta \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed | -   | 50  | 100 | mV  |      |
| V <sub>BEsat</sub>                                      | base-emitter saturation voltage   | $I_C$ = 50 mA; $I_B$ = 5 mA; $t_p \le 300$ μs;<br>pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C                           | -   | -   | 950 | mV   |
| C <sub>c</sub>  | collector capacitance   | $V_{CB} = 20 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$          | -   | 7.5 | -   | pF   |
| C <sub>e</sub>  | emitter capacitance   | $V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$<br>$f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ | -   | 710 | -   | pF   |

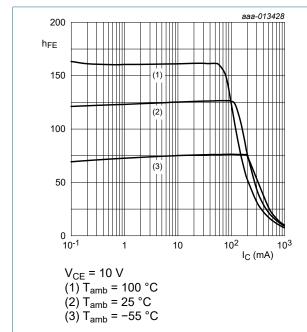


Fig. 4. DC current gain as a function of collector current; typical values

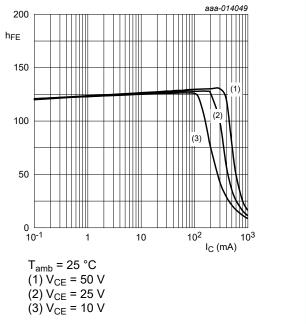


Fig. 5. DC current gain as a function of collector current; typical values

#### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

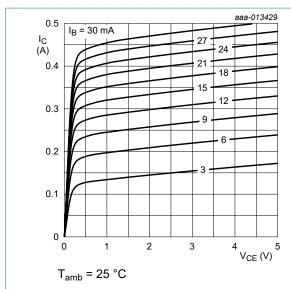
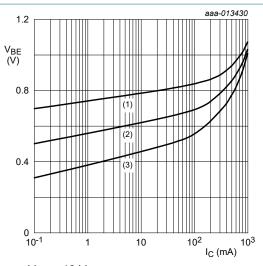


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



V<sub>CE</sub> = 10 V (1) T<sub>amb</sub> = -55 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values

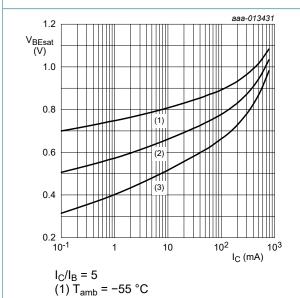
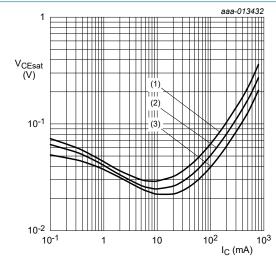


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

(2) T<sub>amb</sub> = 25 °C

(3) T<sub>amb</sub>= 100 °C



 $I_{\rm C}/I_{\rm B} = 5$ (1)  $T_{\rm amb} = 100~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$ 

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

#### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

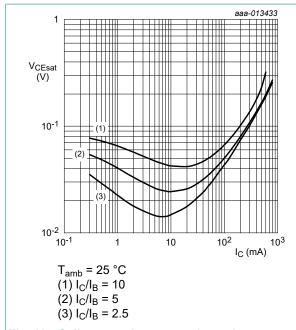


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

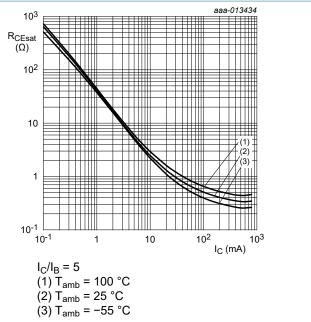
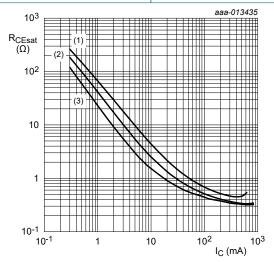


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values



 $T_{amb} = 25 \,^{\circ}C$ (1)  $I_C/I_B = 10$ (2)  $I_C/I_B = 5$ (3)  $I_C/I_B = 2.5$ 

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

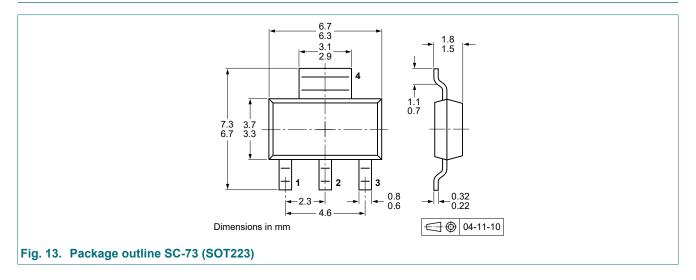
600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

## 11. Test information

#### **Quality information**

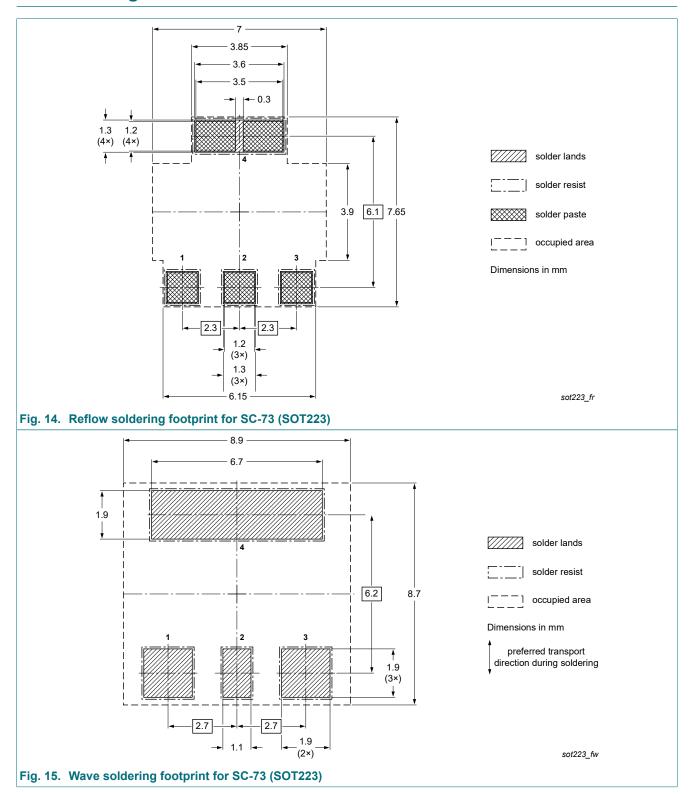
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

# 13. Soldering



## 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID  | Release date        | Data sheet status                             | Change notice | Supersedes    |  |  |  |  |
|----------------|---------------------|---|---------------|---------------|--|--|--|--|
| PBHV8560Z v.2  | 20200907            | Product data sheet                            | -             | PBHV8560Z v.1 |  |  |  |  |
| Modifications: | Characteristics: Le | Characteristics: Legend corrected at Figure 5 |               |               |  |  |  |  |
| PBHV8560Z v.1  | 20150313            | Product data sheet                            | -             | -             |  |  |  |  |

#### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

## 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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PBHV8560Z

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### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

## **Contents**

| 1.  | General description     | . 1 |
|-----|-------------------------|-----|
| 2.  | Features and benefits   | . 1 |
| 3.  | Applications            | . 1 |
| 4.  | Quick reference data    | . 1 |
| 5.  | Pinning information     | . 2 |
| 6.  | Ordering information    | . 2 |
| 7.  | Marking                 | . 2 |
| 8.  | Limiting values         | . 3 |
| 9.  | Thermal characteristics | 4   |
| 10. | Characteristics         | . 5 |
| 11. | Test information        | . 8 |
| 12. | Package outline         | . 8 |
| 13. | Soldering               | . 9 |
|     | Revision history        |     |
|     | Legal information       |     |
|     |                         |     |

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